

## IN THE CLAIMS

The following is a complete listing of the claims, and replaces all earlier versions and listings.

1. - 47. (Canceled)

48. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, an electroconductive film having a fissure, and a step of forming on the electroconductive film and within the fissure, a deposit containing carbon as a principal constituent by connecting the deposit to the electroconductive film, wherein the deposit is formed so that a gap narrower than the fissure is formed within the fissure.

49. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, an electroconductive film composed of an electroconductive material and having a fissure, and a step of forming on the electroconductive film and within the fissure, a deposit containing a material different from the electroconductive material, as a principal constituent by connecting the deposit to the electroconductive film, wherein the deposit is formed so that a gap narrower than the fissure is formed within the fissure.

50. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, a pair of electroconductive films spaced apart by a first gap, and a step of forming on at least one of the electroconductive films and within the first gap, a film containing carbon as a principal constituent by connecting the film to the at least one of the electroconductive films, wherein the film containing carbon is formed so that a second gap narrower than the first gap is formed within the first gap.

51. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, a pair of electroconductive films each comprising an electroconductive material, the electroconductive films being spaced apart by a first gap, and a step of forming on at least one of the electroconductive films and within the first gap, a film containing a material different from the electroconductive material, as a principal constituent by connecting the film to the at least one of the electroconductive films, wherein the film containing the material different from the electroconductive material is formed so that a second gap narrower than the first gap is formed within the first gap.

52. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, a pair of electroconductive films spaced apart by a first gap, and a step of forming on the electroconductive films and within the first gap, a film containing carbon as a principal constituent by connecting the film to the

electroconductive films, wherein the film containing carbon as the principal constituent is formed so that a second gap narrower than the first gap is formed within the first gap.

53. (New) A method of manufacturing an electron-emitting device, comprising a step of forming on a substrate, a pair of electroconductive films each comprising an electroconductive material, the electroconductive films being spaced apart by a first gap, and a step of forming on the electroconductive films and within the first gap, a film containing a material different from the electroconductive material, as a principal constituent by connecting the film to the electroconductive films, wherein the film containing the material different from the electroconductive material is formed so that a second gap narrower than the first gap is formed within the first gap.--